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What is "Embedded - Microcontrollers"?

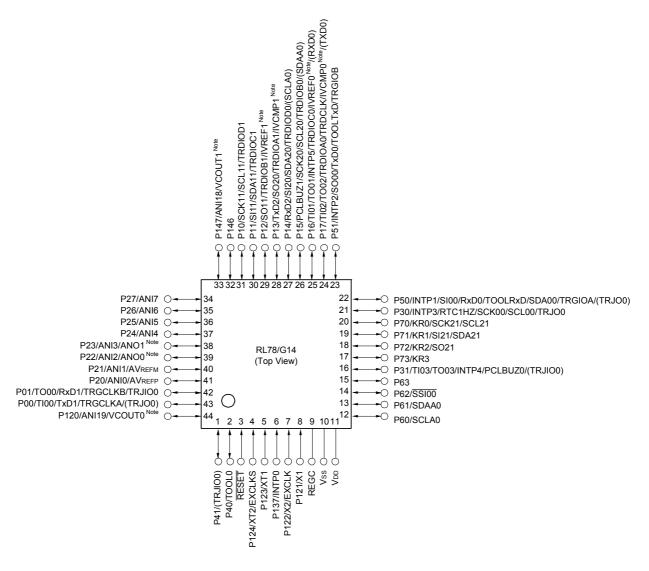
"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	384KB (384K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104lkafa-30

1.3.5 44-pin products

• 44-pin plastic LQFP (10 × 10 mm, 0.8 mm pitch)



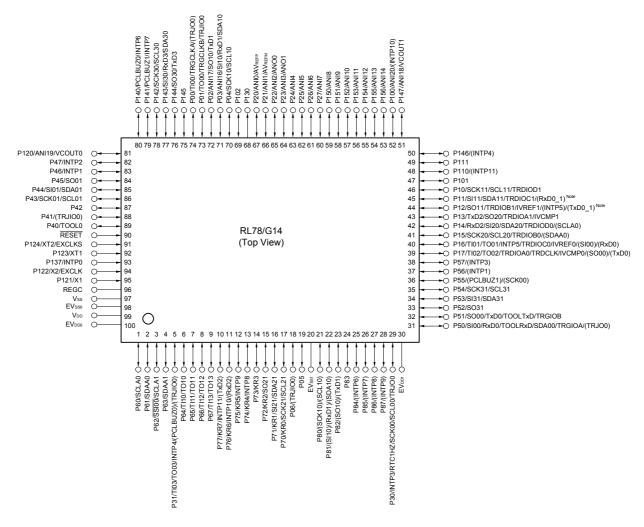
Note Mounted on the 96 KB or more code flash memory products.

Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).

Remark 1. For pin identification, see 1.4 Pin Identification.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

• 100-pin plastic LQFP (14 × 20 mm, 0.65 mm pitch)



Note Mounted on the 384 KB or more code flash memory products.

- Caution 1. Make EVsso, EVss1 pins the same potential as Vss pin.
- Caution 2. Make VDD pin the potential that is higher than EVDD0, EVDD1 pins (EVDD0 = EVDD1).
- Caution 3. Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).
- Remark 1. For pin identification, see 1.4 Pin Identification.
- Remark 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD, EVDD0 and EVDD1 pins and connect the Vss, EVss0 and EVss1 pins to separate ground lines.
- **Remark 3.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

Note

The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F104xD (x = A to C, E to G, J, L): Start address FE900H R5F104xE (x = A to C, E to G, J, L): Start address FE900H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

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		30-pin	32-pin	36-pin	40-pin				
l ¹	tem	R5F104Ax	R5F104Bx	R5F104Cx	R5F104Ex				
		(x = A, C to E)	(x = A, C to E)	(x = A, C to E)	(x = A, C to E)				
Clock output/buzzer	output	2	2	2	2				
		[30-pin, 32-pin, 36-pin products] • 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: fmain = 20 MHz operation) [40-pin products] • 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: fmain = 20 MHz operation) • 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: fsub = 32.768 kHz operation)							
8/10-bit resolution A	/D converter	8 channels	8 channels	8 channels	9 channels				
Serial interface		[30-pin, 32-pin products] • CSI: 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I ² C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I ² C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I ² C: 1 channel [36-pin, 40-pin products] • CSI: 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I ² C: 1 channel • CSI: 2 channel/UART: 1 channel/simplified I ² C: 2 channels							
	I ² C bus	1 channel	1 channel	1 channel	1 channel				
Data transfer contro	ller (DTC)	28 sources			29 sources				
Event link controller	(ELC)	Event input: 19 Event input: 20 Event trigger output: 7 Event trigger output: 7							
Vectored interrupt	Internal	24	24	24	24				
sources	External	6	6	6	7				
Key interrupt	1	_	_	_	4				
Reset		Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution Note Internal reset by RAM parity error Internal reset by illegal-memory access							
Power-on-reset circuit		Power-on-reset:							
Voltage detector		1.63 V to 4.06 V (14 stages)							
On-chip debug function		Provided			-				
Power supply voltag	e	V _{DD} = 1.6 to 5.5 V (T _A = -40 to +85°C) V _{DD} = 2.4 to 5.5 V (T _A = -40 to +105°C)							
Operating ambient to	emperature	$T_A = -40 \text{ to } +85^{\circ}\text{C}$ (A: Consumer applications, D: Industrial applications), $T_A = -40 \text{ to } +105^{\circ}\text{C}$ (G: Industrial applications)							

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not is issued by emulation with the in-circuit emulator or on-chip debug emulator.

[30-pin, 32-pin, 36-pin, 40-pin products (code flash memory 96 KB to 256 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

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		30-pin	32-pin	36-pin	40-pin			
ı	Item	R5F104Ax (x = F, G)	R5F104Bx $(x = F, G)$	R5F104Cx (x = F, G)	R5F104Ex (x = F to H)			
Code flash mem	nory (KB)	96 to 128	96 to 128	96 to 128	96 to 192			
Data flash mem	ory (KB)	8	8	8	8			
RAM (KB)		12 to 16 Note	12 to 16 Note	12 to 16 Note	12 to 20 Note			
Address space		1 MB						
Main system clock	High-speed system clock High-speed on-chip oscillator clock (fiн)	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) mode: 1 to 20 MHz (VDD = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (VDD = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (VDD = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (VDD = 1.6 to 5.5 V) HS (high-speed main) mode: 1 to 32 MHz (VDD = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (VDD = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (VDD = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (VDD = 1.6 to 5.5 V)						
Subsystem cloc	k		_		XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz			
Low-speed on-c	chip oscillator clock	15 kHz (TYP.): VDD = 1.6	to 5.5 V		•			
General-purpose	e register	8 bits × 32 registers (8 bits	s × 8 registers × 4 banks)					
Minimum instruc	ction execution time	0.03125 μs (High-speed on-chip oscillator clock: fiн = 32 MHz operation)						
		0.05 μs (High-speed system clock: f _{MX} = 20 MHz operation)						
		— 30.5 μs (Subsystem clock: fsub = 32.768 kH operation)						
Instruction set		Multiplication and Accur		+ 32 bits)	,			
I/O port	Total	26	28	32	36			
	CMOS I/O	21	22	26	28			
	CMOS input	3	3	3	5			
	CMOS output	_	_	_	_			
	N-ch open-drain I/O (6 V tolerance)	2	3	3	3			
Timer	16-bit timer	8 channels (TAU: 4 channels, Timer RJ: 1 channel, Timer RD: 2 channels, Timer RG: 1 channel)						
	Watchdog timer	1 channel						
	Real-time clock (RTC)	1 channel						
	12-bit interval timer	1 channel						
	Timer output	Timer outputs: 13 channe PWM outputs: 9 channels						
	RTC output		_		1 • 1 Hz (subsystem clock: fsub = 32.768 kHz)			

(Note is listed on the next page.)

[44-pin, 48-pin, 52-pin, 64-pin products (code flash memory 16 KB to 64 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

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					(1/2			
		44-pin	48-pin	52-pin	64-pin			
	Item	R5F104Fx	R5F104Gx	R5F104Jx	R5F104Lx			
		(x = A, C to E)	(x = A, C to E)	(x = C to E)	(x = C to E)			
Code flash me	mory (KB)	16 to 64	16 to 64	32 to 64	32 to 64			
Data flash men	nory (KB)	4	4	4	4			
RAM (KB)		2.5 to 5.5 Note	2.5 to 5.5 Note	4 to 5.5 Note	4 to 5.5 Note			
Address space		1 MB						
Main system clock	High-speed system clock	HS (high-speed main) HS (high-speed main) LS (low-speed main) n	scillation, external main mode: 1 to 20 MHz (V mode: 1 to 16 MHz (V node: 1 to 8 MHz (VD mode: 1 to 4 MHz (VD	DD = 2.7 to 5.5 V), DD = 2.4 to 5.5 V), D = 1.8 to 5.5 V),	(CLK)			
	High-speed on-chip oscillator clock (fін)	HS (high-speed main)	mode: 1 to 32 MHz (V mode: 1 to 16 MHz (V node: 1 to 8 MHz (VD mode: 1 to 4 MHz (VD	DD = 2.4 to 5.5 V), D = 1.8 to 5.5 V),				
Subsystem clo	ck	XT1 (crystal) oscillation	n, external subsystem o	lock input (EXCLKS) 3	2.768 kHz			
Low-speed on-	chip oscillator clock	15 kHz (TYP.): VDD = 1	I.6 to 5.5 V					
General-purpos	se register	8 bits × 32 registers (8 bits × 8 registers × 4 banks)						
Minimum instruction execution time		0.03125 μs (High-spee	ed on-chip oscillator clo	ck: fін = 32 MHz operat	ion)			
		0.05 μs (High-speed system clock: f _{MX} = 20 MHz operation)						
		30.5 μs (Subsystem cl	ock: fsuв = 32.768 kHz	operation)				
Instruction set		Multiplication (8 bits : Multiplication and Ac	its) /logical operation (8/16 < 8 bits, 16 bits × 16 bits cumulation (16 bits × 16 nd bit manipulation (Se	s), Division (16 bits ÷ 16 6 bits + 32 bits)				
I/O port	Total	40	44	48	58			
	CMOS I/O	31	34	38	48			
	CMOS input	5	5	5	5			
	CMOS output	_	1	1	1			
	N-ch open-drain I/O (6 V tolerance)	4	4	4	4			
Timer	16-bit timer	8 channels (TAU: 4 channels, Timer RJ: 1 channel, Timer RD: 2 channels, Timer RG: 1 channel)						
	Watchdog timer	1 channel						
	Real-time clock (RTC)	1 channel						
	12-bit interval timer	1 channel						
	Timer output	Timer outputs: 13 char PWM outputs: 9 chann						
	RTC output	1 • 1 Hz (subsystem clock: fsuB = 32.768 kHz)						

(Note is listed on the next page.)

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		40 :	(2/2)			
lta m		48-pin	64-pin			
Item		R5F104Gx	R5F104Lx			
		(x = K, L)	(x = K, L)			
Clock output/buzzer outp	out	2	2			
		• 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5	5 MHz, 5 MHz, 10 MHz			
		(Main system clock: fMAIN = 20 MHz operation				
		• 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz				
		(Subsystem clock: fsub = 32.768 kHz opera	· T			
8/10-bit resolution A/D co	onverter	10 channels	12 channels			
D/A converter		2 channels				
Comparator		2 channels				
Serial interface		[48-pin products]				
		CSI: 2 channels/UART (UART supporting LI	N-bus): 1 channel/simplified I ² C: 2 channels			
		CSI: 1 channel/UART: 1 channel/simplified I	² C: 1 channel			
		CSI: 2 channels/UART: 1 channel/simplified	I ² C: 2 channels			
		[64-pin products]				
		• CSI: 2 channels/UART (UART supporting LIN-bus): 1 channel/simplified I ² C: 2 channels				
		• CSI: 2 channels/UART: 1 channel/simplified I ² C: 2 channels				
		CSI: 2 channels/UART: 1 channel/simplified I ² C: 2 channels				
	I ² C bus	1 channel	1 channel			
Data transfer controller (DTC)		32 sources 33 sources				
Event link controller (ELC	C)	Event input: 22				
		Event trigger output: 9				
Vectored interrupt	Internal	24	24			
sources	External	10	13			
Key interrupt		6	8			
Reset		Reset by RESET pin				
l		Internal reset by watchdog timer				
		Internal reset by power-on-reset				
		Internal reset by voltage detector				
		Internal reset by illegal instruction execution	Note			
		Internal reset by RAM parity error				
		Internal reset by illegal-memory access				
Power-on-reset circuit		• Power-on-reset: 1.51 ±0.04 V (T _A = -40	· · · · · · · · · · · · · · · · · · ·			
		1.51 ± 0.06 V (TA = -40 • Power-down-reset: 1.50 ± 0.04 V (TA = -40	•			
		Power-down-reset: 1.50 \pm 0.04 V (TA = -40 to +85°C) 1.50 \pm 0.06 V (TA = -40 to +105°C)				
Voltage detector		1.63 V to 4.06 V (14 stages)				
On-chip debug function		Provided				
Power supply voltage		V _{DD} = 1.6 to 5.5 V (T _A = -40 to +85°C)				
1 Ower Supply Voltage		V _{DD} = 2.4 to 5.5 V (T _A = -40 to +105°C)				
Operating ambient temper	erature	, ,	D: Industrial applications)			
	Jature	TA = -40 to +85°C (A: Consumer applications, D: Industrial applications), TA = -40 to +105°C (G: Industrial applications)				
		(3. madound applications	,			

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution is not issued by emulation with the in-circuit emulator or on-chip debug emulator.

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			(212)			
		80-pin	100-pin			
lt.	tem	R5F104Mx	R5F104Px			
		(x = F to H, J)	(x = F to H, J)			
Clock output/buzz	zer output	2	2			
		 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.3 (Main system clock: fmain = 20 MHz operations 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.09 (Subsystem clock: fsub = 32.768 kHz operations) 	on) 96 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz			
8/10-bit resolution	A/D converter	17 channels	20 channels			
D/A converter		2 channels	2 channels			
Comparator		2 channels	2 channels			
Serial interface		CSI: 2 channels/UART: 1 channel/simplified CSI: 2 channels/UART: 1 channel/simplified	[80-pin, 100-pin products] • CSI: 2 channels/UART (UART supporting LIN-bus): 1 channel/simplified I ² C: 2 channels • CSI: 2 channels/UART: 1 channel/simplified I ² C: 2 channels • CSI: 2 channels/UART: 1 channel/simplified I ² C: 2 channels • CSI: 2 channels/UART: 1 channel/simplified I ² C: 2 channels			
	I ² C bus	2 channels	2 channels			
Data transfer con	troller (DTC)	39 sources	39 sources			
Event link controll	er (ELC)	Event input: 26 Event trigger output: 9	· ·			
Vectored inter-	Internal	32	32			
rupt sources	External	13	13			
Key interrupt	1	8	8			
Reset		Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution Note Internal reset by RAM parity error Internal reset by illegal-memory access				
Power-on-reset circuit		 Power-on-reset: 1.51 ±0.04 V (TA = -40 to +85°C) 1.51 ±0.06 V (TA = -40 to +105°C) Power-down-reset: 1.50 ±0.04 V (TA = -40 to +85°C) 1.50 ±0.06 V (TA = -40 to +105°C) 				
Voltage detector		1.63 V to 4.06 V (14 stages)				
On-chip debug fu	nction	Provided				
Power supply volt	age	V _{DD} = 1.6 to 5.5 V (T _A = -40 to +85°C) V _{DD} = 2.4 to 5.5 V (T _A = -40 to +105°C)				
Operating ambier	nt temperature	T _A = -40 to +85°C (A: Consumer applications, D: Industrial applications), T _A = -40 to +105°C (G: Industrial applications)				

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution is not issued by emulation with the in-circuit emulator or on-chip debug emulator.

2.3 DC Characteristics

2.3.1 Pin characteristics

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	Іон1	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	1.6 V ≤ EVDD0 ≤ 5.5 V			-10.0 Note 2	mA
		Total of P00 to P04, P40 to P47,	4.0 V ≤ EVDD0 ≤ 5.5 V			-55.0	mA
		(When duty ≤ 70% Note 3) 1.8	2.7 V ≤ EV _{DD0} < 4.0 V			-10.0	mA
			1.8 V ≤ EVDD0 < 2.7 V			-5.0	mA
			1.6 V ≤ EV _{DD0} < 1.8 V			-2.5	mA
		Total of P05, P06, P10 to P17,	4.0 V ≤ EVDD0 ≤ 5.5 V			-80.0	mA
		P30, P31, P50 to P57,	2.7 V ≤ EVDD0 < 4.0 V			-19.0	mA
		P64 to P67, P70 to P77, P80 to P87, P100, P101, P110,	1.8 V ≤ EVDD0 < 2.7 V			-10.0	mA
		P111, P146, P147 (When duty ≤ 70% Note 3)	1.6 V ≤ EVDD0 < 1.8 V			-5.0	mA
	Total of all pins (When duty ≤ 70% Note 3)	1.6 V ≤ EVDD0 ≤ 5.5 V			-135.0 Note 4	mA	
	IOH2 Per pin for P20 to P27, P150 to P156	· '	1.6 V ≤ VDD ≤ 5.5 V			-0.1 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	1.6 V ≤ VDD ≤ 5.5 V			-1.5	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from the EVDDO, EVDD1, VDD pins to an output pin.

Note 3. Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = (IoH \times 0.7)/(n \times 0.01) <Example> Where n = 80% and IoH = -10.0 mA Total output current of pins = (-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.

A current higher than the absolute maximum rating must not flow into one pin.

Note 4. -100 mA for industrial applications (R5F104xxDxx, R5F104xxGxx).

Caution P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Note 2. Do not exceed the total current value.

- Note 1. Total current flowing into VDD and EVDD0, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0 or Vss, EVss0. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing data flash rewrite.
- Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.
- **Note 3.** When high-speed system clock and subsystem clock are stopped.
- Note 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
- Note 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 32 MHz

 $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V@1 MHz to 16 MHz}$

LS (low-speed main) mode: 1.8 V \leq VDD \leq 5.5 V@1 MHz to 8 MHz LV (low-voltage main) mode: 1.6 V \leq VDD \leq 5.5 V@1 MHz to 4 MHz

- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHoco: High-speed on-chip oscillator clock frequency (64 MHz max.)
- Remark 3. fin: High-speed on-chip oscillator clock frequency (32 MHz max.)
- Remark 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

- Note 1. Total current flowing into VDD, EVDD0, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0, and EVDD1, or Vss, EVss0, and EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 3. When high-speed system clock and subsystem clock are stopped.
- **Note 4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.
- Note 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz to } 32 \text{ MHz}$

 $2.4~V \leq V_{DD} \leq 5.5~V \textcircled{@}1~MHz$ to 16 MHz

LS (low-speed main) mode: 1.8 V \leq VDD \leq 5.5 V@1 MHz to 8 MHz LV (low-voltage main) mode: 1.6 V \leq VDD \leq 5.5 V@1 MHz to 4 MHz

- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHoco: High-speed on-chip oscillator clock frequency (64 MHz max.)
 Remark 3. fH: High-speed on-chip oscillator clock frequency (32 MHz max.)
 Remark 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

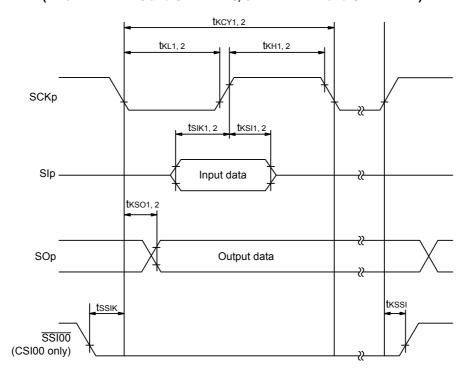
(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Parameter	er Symbol Conditions		ditions	HS (high-spee	d main)	LS (low-speed mode	d main)	LV (low-voltag mode	e main)	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle	tkcy2	4.0 V ≤ EVDD0 ≤ 5.5 V	20 MHz < fmck	8/fмск		_		_		ns
time Note 5			fмcк ≤ 20 MHz	6/fмск		6/fмск		6/fмск		ns
		2.7 V ≤ EVDD0 ≤ 5.5 V	16 MHz < fmck	8/fмск		_		_		ns
			fмcк ≤ 16 MHz	6/fмск		6/fмск		6/fмск		ns
		2.4 V ≤ EVDD0 ≤ 5.5 V		6/fмск and 500		6/fмск and 500		6/fмск and 500		ns
		1.8 V ≤ EVDD0 ≤ 5.5 V		6/fмск and 750		6/fмск and 750		6/fмск and 750		ns
		1.7 V ≤ EV _{DD0} ≤ 5.5 V		6/fмск and 1500		6/fмск and 1500		6/fмск and 1500		ns
		1.6 V ≤ EV _{DD0} ≤ 5.5 V		_		6/fмск and 1500		6/fмск and 1500		ns
SCKp high-/	tĸн2,	4.0 V ≤ EVDD0 ≤ 5.5 V		tkcy2/2 - 7		tkcy2/2 - 7		tkcy2/2 - 7		ns
low-level width		2.7 V ≤ EV _{DD0} ≤ 5.5 V		tkcy2/2 - 8		tkcy2/2 - 8		tkcy2/2 - 8		ns
		1.8 V ≤ EVDD0 ≤ 5.5 V	1.8 V ≤ EVDD0 ≤ 5.5 V			tkcy2/2 - 18		tkcy2/2 - 18		ns
	1.7 V ≤ EV _{DD0} ≤ 5.5 V			tkcy2/2 - 66		tkcy2/2 - 66		tkcy2/2 - 66		ns
		1.6 V ≤ EVDD0 ≤ 5.5 V		_		tkcy2/2 - 66		tkcy2/2 - 66		ns
SIp setup time	tsık2	2.7 V ≤ EVDD0 ≤ 5.5 V		1/fмск + 20		1/fмск + 30		1/fмск + 30		ns
(to SCKp↑) Note 1		1.8 V ≤ EVDD0 ≤ 5.5 V		1/fмск + 30		1/fмск + 30		1/fмск + 30		ns
		1.7 V ≤ EVDD0 ≤ 5.5 V		1/fмск + 40		1/fмск + 40		1/fмск + 40		ns
		1.6 V ≤ EVDD0 ≤ 5.5 V		_		1/fмск + 40		1/fмск + 40		ns
SIp hold time	tks12	1.8 V ≤ EVDD0 ≤ 5.5 V		1/fмск + 31		1/fмск + 31		1/fмск + 31		ns
(from SCKp↑) Note 2		1.7 V ≤ EV _{DD0} ≤ 5.5 V		1/fмск + 250		1/fмск + 250		1/fмск + 250		ns
		1.6 V ≤ EVDD0 ≤ 5.5 V		_		1/fмск + 250		1/fмск + 250		ns
Delay time from SCKp↓ to	tkso2	C = 30 pF Note 4	2.7 V ≤ EV _{DD0} ≤ 5.5 V		2/fмск + 44		2/fмск + 110		2/fмск + 110	ns
SOp output Note 3			2.4 V ≤ EV _{DD0} ≤ 5.5 V		2/fмск + 75		2/fмск + 110		2/fмск + 110	ns
			1.8 V ≤ EV _{DD0} ≤ 5.5 V		2/fмcк + 100		2/fмск + 110		2/fмск + 110	ns
			1.7 V ≤ EV _{DD0} ≤ 5.5 V		2/fмcк + 220		2/fмск + 220		2/fмск + 220	ns
		_	1.6 V ≤ EV _{DD0} ≤ 5.5 V		_		2/fмск + 220		2/fмск + 220	ns

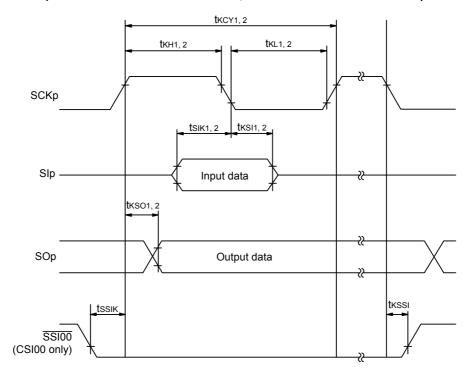
- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. C is the load capacitance of the SOp output lines.
- **Note 5.** The maximum transfer rate when using the SNOOZE mode is 1 Mbps.
- Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



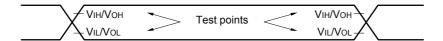
CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



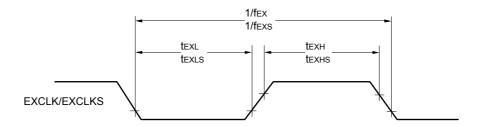
Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31)

Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

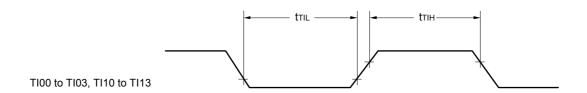
AC Timing Test Points

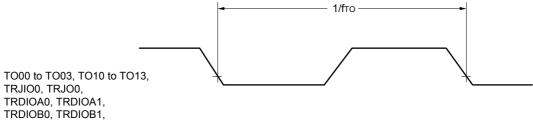


External System Clock Timing



TI/TO Timing



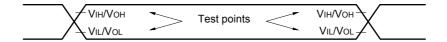


TRDIOCO, TRDIOC1, TRDIODO, TRDIOD1,

TRGIOA, TRGIOB

3.5 Peripheral Functions Characteristics

AC Timing Test Points



3.5.1 Serial array unit

(1) During communication at same potential (UART mode)

(TA = -40 to +105°C, 2.4 V \leq EVDD0 = EVDD1 \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions	HS (high-spee	ed main) Mode	Unit
			MIN.	MAX.	
Transfer rate Note 1		2.4 V ≤ EVDD0 ≤ 5.5 V		fMCK/12 Note 2	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note 3		2.6	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

However, the SNOOZE mode cannot be used when FRQSEL4 = 1.

Note 2. The following conditions are required for low voltage interface when EVDD0 < VDD.

 $2.4 \text{ V} \le \text{EV}_{DD0} < 2.7 \text{ V: MAX. } 1.3 \text{ Mbps}$

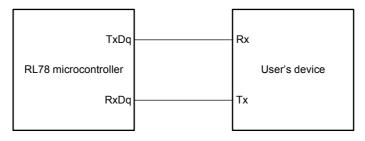
Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 32 MHz (2.7 V \leq VDD \leq 5.5 V)

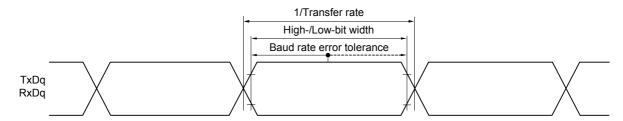
16 MHz (2.4 V \leq VDD \leq 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



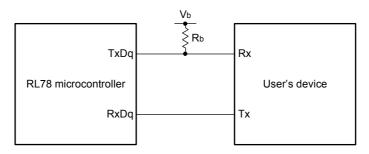
Remark 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 5, 14)

Remark 2. fmck: Serial array unit operation clock frequency

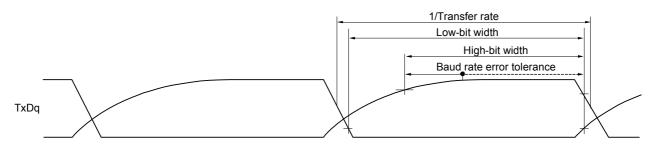
 $(Operation \ clock \ to \ be \ set \ by \ the \ CKSmn \ bit \ of \ serial \ mode \ register \ mn \ (SMRmn). \ m: \ Unit \ number,$

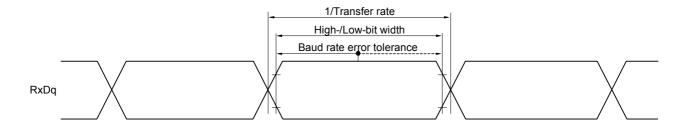
n: Channel number (mn = 00 to 03, 10 to 13))

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





- **Remark 1.** $Rb[\Omega]$: Communication line (TxDq) pull-up resistance,
 - Cb[F]: Communication line (TxDq) load capacitance, Vb[V]: Communication line voltage
- Remark 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 5, 14)
- Remark 3. fmck: Serial array unit operation clock frequency
 - (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
 - m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))
- Remark 4. UART2 cannot communicate at different potential when bit 1 (PIOR01) of peripheral I/O redirection register 0 (PIOR0) is

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

(TA = -40 to +105°C, 2.4 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(2/3)

Parameter	Symbol	Conditions	HS (high-spee	ed main) mode	Unit
			MIN.	MAX.	
SIp setup time (to SCKp↑) Note	tsıkı	$ 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega $	162		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	354		ns
		$2.4 \ V \le EV_{DD0} < 3.3 \ V,$ $1.6 \ V \le V_b \le 2.0 \ V,$ $C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega$	958		ns
SIp hold time (from SCKp†) Note	tksi1	$ 4.0 \text{ V} \leq \text{EV}_{\text{DDO}} \leq 5.5 \text{ V}, \\ 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ \text{C}_{\text{b}} = 30 \text{ pF}, \text{R}_{\text{b}} = 1.4 \text{ k}\Omega $	38		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	38		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DDO}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 5.5 \text{ k}\Omega$	38		ns
Delay time from SCKp↓ to SOp output Note	tkso1	$4.0 \text{ V} \le \text{EV}_{\text{DDO}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 1.4 \text{ k}\Omega$		200	ns
		$\begin{split} 2.7 \ V &\leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V &\leq V_{b} \leq 2.7 \ V, \\ C_{b} &= 30 \ pF, \ R_{b} = 2.7 \ k \Omega \end{split}$		390	ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DDO}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, \text{ Rb} = 5.5 \text{ k}\Omega$		966	ns

Note When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

(TA = -40 to +105°C, 2.4 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Parameter	Symbol	Conditions	HS (high-spee	ed main) mode	Unit
			MIN.	MAX.	
SIp setup time (to SCKp↓) Note	tsıĸ1	$ 4.0 \text{ V} \leq \text{EV}_{\text{DDO}} \leq 5.5 \text{ V}, \\ 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, \text{ Rb} = 1.4 \text{ k}\Omega $	88		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	88		ns
		$2.4 \ V \le EV_{DD0} < 3.3 \ V,$ $1.6 \ V \le V_b \le 2.0 \ V,$ $C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega$	220		ns
SIp hold time (from SCKp↓) ^{Note}	tksi1	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 1.4 \text{ k}\Omega$	38		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	38		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DDO}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 5.5 \text{ k}\Omega$	38		ns
Delay time from SCKp↑ to SOp output Note	tkso1	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 1.4 \text{ k}\Omega$		50	ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$		50	ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, \text{ R}_{\text{b}} = 5.5 \text{ k}\Omega$		50	ns

Note When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

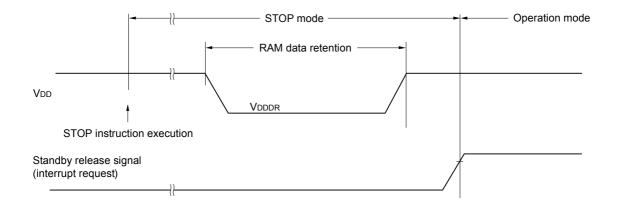
(3/3)

3.7 RAM Data Retention Characteristics

$(TA = -40 \text{ to } +105^{\circ}\text{C}, Vss = 0V)$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.44 Note		5.5	V

Note The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.



3.8 Flash Memory Programming Characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	fclk	$2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$	1		32	MHz
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years T _A = 85°C Note 4	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 year TA = 25°C		1,000,000		
		Retained for 5 years TA = 85°C Note 4	100,000			
		Retained for 20 years TA = 85°C Note 4	10,000			

- Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
- Note 2. When using flash memory programmer and Renesas Electronics self-programming library
- **Note 3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.
- **Note 4.** This temperature is the average value at which data are retained.

3.9 Dedicated Flash Memory Programmer Communication (UART)

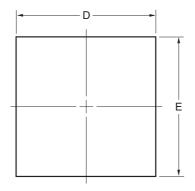
(TA = -40 to +105°C, 2.4 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

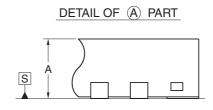
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

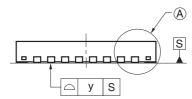
4.2 32-pin products

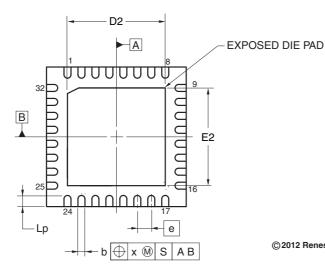
R5F104BAANA, R5F104BCANA, R5F104BDANA, R5F104BEANA, R5F104BFANA, R5F104BGANA R5F104BADNA, R5F104BCDNA, R5F104BDNA, R5F104BEDNA, R5F104BFDNA, R5F104BGDNA R5F104BAGNA, R5F104BCGNA, R5F104BDGNA, R5F104BEGNA, R5F104BGNA, R5F104BGNA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]	
P-HWQFN32-5x5-0.50	PWQN0032KB-A	P32K8-50-3B4-4	0.06	









Referance	Dimension in Millimeters						
Symbol	Min	Nom	Max				
D	4.95	5.00	5.05				
Е	4.95	5.00	5.05				
Α	0.70	0.75	0.80				
b	0.18	0.25	0.30				
е		0.50	_				
Lp	0.30	0.40	0.50				
х			0.05				
у	_	_	0.05				

	ITEM		D2			E2		
			MIN	NOM	MAX	MIN	MOM	MAX
	EXPOSED DIE PAD VARIATIONS	Α	3.45	3.50	3.55	3.45	3.50	3.55

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